Abstracts

A W-Band Monolithic Amplifier

N. Camilleri, P. Chye, P. Gregory and A. Lee. "A W-Band Monolithic Amplifier." 1990 MTT-S International Microwave Symposium Digest 90.2 (1990 Vol. II [MWSYM]): 903-906.

Monolithic amplifiers at 90 GHz have been fabricated using 75µm GaAs MESFET and Pseudomorphic HEMT (PHEMT) devices. The sub .2µm gate length PHEMT devices have demonstrated an F/sub t/ of 100GHz and an F/sub max/ of 200GHz. Monolithic MESFET and PHEMT single stage amplifiers have achieved 3.5 dB and 7 dB gain respectively at 90 GHz.

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